

## **KSH13007DT**

对应国外型号 FJP3307D

## ■ 主要用途

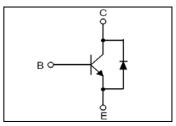
高压快速开关。电子节能灯、开关电源等应用

## **■ 极限值** (T<sub>a</sub>=25℃)

| T <sub>stg</sub> ——贮存温度······ -55~150℃                   |
|--|
| T <sub>j</sub> ——结温······ 150℃                           |
| P <sub>C</sub> ——集电极功率耗散(T <sub>c</sub> =25℃)······· 65W |
| V <sub>CBO</sub> ——集电极—基极电压······ 700V                   |
| V <sub>CEO</sub> ——集电极—发射极电压······ 400V                  |
| V <sub>EBO</sub> ——发射极—基极电压····· 9V                      |
| I <sub>C</sub> ——集电极电流(DC)                               |
| I <sub>C</sub> ——集电极电流(脉冲)                               |
| I <sub>B</sub> ——基极电流·······4A                           |

## ■ 外形图及引脚排列





### **■ 电参数** (T<sub>a</sub>=25℃)

| 参数符号      | 符号说明        | 最小值 | 典型值 | 最大值  | 单 位 | 测 试 条 件   |
|-----------|-------------|-----|-----|------|-----|---|
| ВУсво     | 集电极一基极击穿电压  | 700 |     |      | V   | Ic=500 μ A, IE=0  |
| BVCEO     | 集电极一发射极击穿电压 | 400 |     |      | V   | Ic=5mA, I <sub>B</sub> =0   |
| BVEBO     | 发射极—基极击穿电压  | 9   |     |      | V   | I <sub>E</sub> =500 μ A, I <sub>C</sub> =0                                |
| Ієво      | 发射极一基极截止电流  |     |     | 1    | mA  | V <sub>EB</sub> =9V, I <sub>C</sub> =0                                    |
| hfe       | 直流电流增益      | 10  |     | 40   |     | Vce=5V, Ic=2A   |
|           |             | 5   |     | 30   |     | Vce=5V, Ic=5A   |
| VCE (sat) | 集电极一发射极饱和电压 |     |     | 1    | V   | Ic=2A, I <sub>B</sub> =0.4A   |
|           |             |     |     | 2    | V   | Ic=5A, I <sub>B</sub> =1A   |
|           |             |     |     | 3    | V   | Ic=8A, I <sub>B</sub> =2A   |
| VBE(sat)  | 基极—发射极饱和电压  |     |     | 1.2  | V   | Ic=2A, I <sub>B</sub> =0.4A   |
|           |             |     |     | 1.6  | V   | Ic=5A, I <sub>B</sub> =1A   |
| $V_{F}$   | 内部二极管正向压降   |     |     | 2. 5 | V   | I <sub>F</sub> =2A  |
| Cob       | 共基极输出电容     |     | 60  |      | pF  | V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz                           |
| ts        | 贮存时间        | 3   |     | 8    | μs  | Vce=5V, Ic=0.5A   |
|           |             |     |     |      |     | (UI9600)  |
| ts        | 贮存时间        |     |     | 3    | μs  | ¬ Vcc=125V, Ic=5A,  |
| tf        | 下降时间        |     |     | 0.7  | μs  | $\int$ I <sub>B1</sub> =-I <sub>B2</sub> =1A, R <sub>L</sub> =50 $\Omega$ |

分档: H1(10--16) H2(14--21) H3(19--26) H4(24--31) H5(29--40)

#### NPN SILICON TRANSISTOR

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### ■ 特性曲线

Figure 1. Static Characterstic

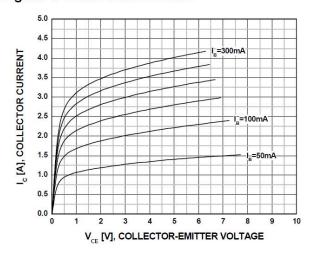


Figure 2. DC Current Gain (H1 Grade)

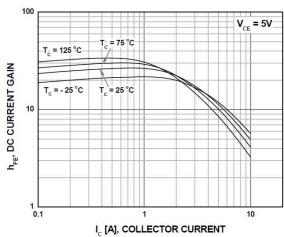


Figure 3. DC Current Gain (H2 Grade)

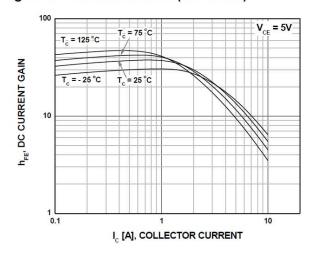


Figure 4. Collector-Emitter Saturation Voltage

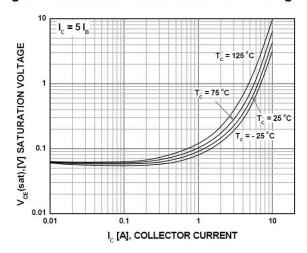


Figure 5. Base-Emitter Saturation Voltage

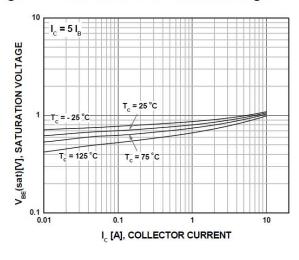
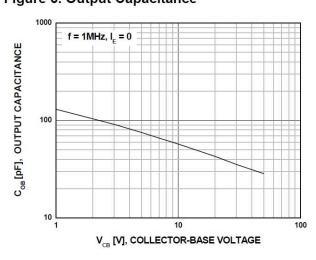


Figure 6. Output Capacitance



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Figure 7. Power Derating

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Tc[°C], CASE TEMPERATURE

Figure 8. Reverse Biased Safe Operating Area

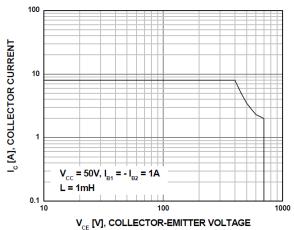


Figure 9. Forward Biased Safe Operating Area

